Transistors 2SD227

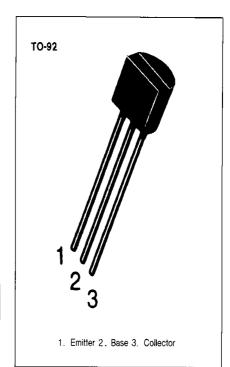


LOW FREQUENCY POWER AMPLIFIER

- Complement to KSA642
- Collector Dissipation Pc = 400mW

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit	
Collector-Base Voltage	V _{CBO}	30	٧	
Collector-Emitter Voltage	V _{CEO}	25	٧	
Emitter-Base Voltage	V _{EBO}	5	٧	
Collector Current	l _c	300	mA	
Collector Dissipation	P _c	400	mW	
Junction Temperature	Ti l	150	∘C	
Storage Temperature	Tstg	-55 ~ 150	°C	



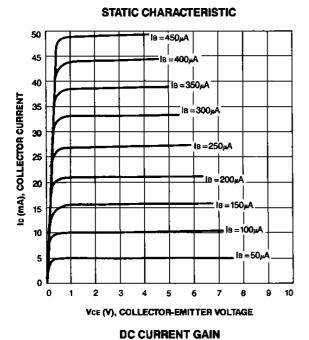
ELECTRICAL CHARACTERISTICS (Ta=25°C)

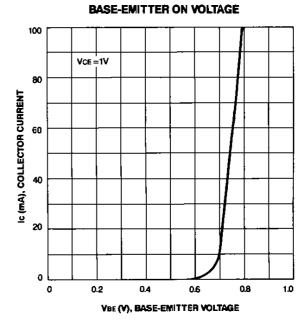
Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	$I_{C} = 100 \mu A, I_{E} = 0$	30			٧
Collector-Emitter Breakdown Voltage	BV _{CEO}	$I_{C}=10\text{mA}, I_{B}=0$	25			V
Emitter-Base Breakdown Voltage	BV _{EBO}	$I_{\rm E} = 10 \mu A$, $I_{\rm C} = 0$	5			٧
Collector Cut-off Current	I _{CBO}	$V_{CB} = 25V, I_{E} = 0$			0.1	μА
Emitter Cut-off Current	I _{EBO}	$V_{EB} = 3V, I_{C} = 0$			0.1	μA
DC Current Gain	h _{FE}	$V_{CE} = 1V, I_{C} = 50 \text{mA}$	70		400	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C =300mA, I _B =30mA		0.14	0.4	٧

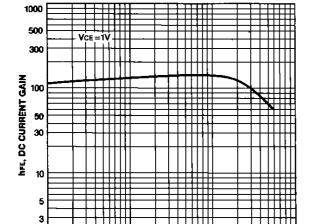
h_{FE} CLASSIFICATION

Classification	0	Y	G
h _{FE}	70-140	120-240	200-400

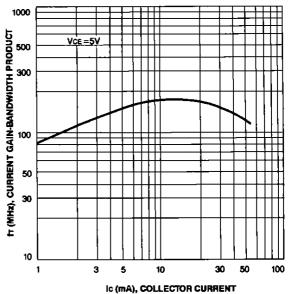














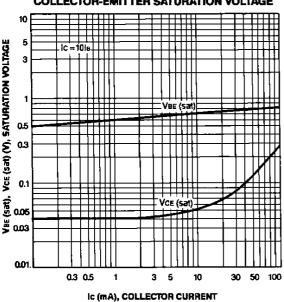
30 50

100

300500 1000

3

Vce (sat) (V), SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE

